



SOT-23 Plastic-Encapsulate Transistors

B772 TRANSISTOR(PNP)

FEATURES

- Complimentary to D882
- Collector Current: $I_c=-1.5A$

MARKING: B772

MAXIMUM RATINGS(TA=25°C unless otherwise noted)

SOT-23



- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

Symbol	Parameter	Value	Units
VCBO	Collector-Base Voltage	-40	V
VCEO	Collector-Emitter Voltage	-30	V
VEBO	Emitter-Base Voltage	-6	V
IC	Collector Current-Continuous	-1.5	A
PC	Collector Power Dissipation	-0.3	W
TJ	Junction Temperature	150	°C
Tatg	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS(Tamb=25°C unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR) _{CBO}	$I_c=-1mA, I_E=0$	-40			V
Collector-emitter breakdown voltage	V(BR) _{CEO}	$I_c=-1mA, I_B=0$	-30			V
Emitter-base breakdown voltage	V(BR) _{EBO}	$I_c=-1mA, I_c=0$	-6			V
Collector cut-off current	ICBO	$V_{CB}=-40V, I_E=0$			-0.1	μA
Collector cut-off current	ICEO	$V_{ce}=-30V, I_B=0$			-0.5	μA
Emitter cut-off current	IEBO	$V_{EB}=-5V, I_c=0$			-0.1	μA
DC current gain	HFE	$V_{ce}=-5V, I_c=-1mA$	60		400	
Collector-emitter saturation voltage	VCE(sat)	$I_c=-80mA, I_B=-80mA$			-0.5	V
Base-emitter saturation voltage	VBE(sat)	$I_c=-80mA, I_B=-80mA$			-1.2	V
Gain Bandwidth Product	Ft	$V_{CE}=-10V, I_c=-50mA, f=30MHz$	100			MHz
Collector output capacitance	Cob	$V_{CB}=-10V, I_E=0, f=1MHz$			20	pF